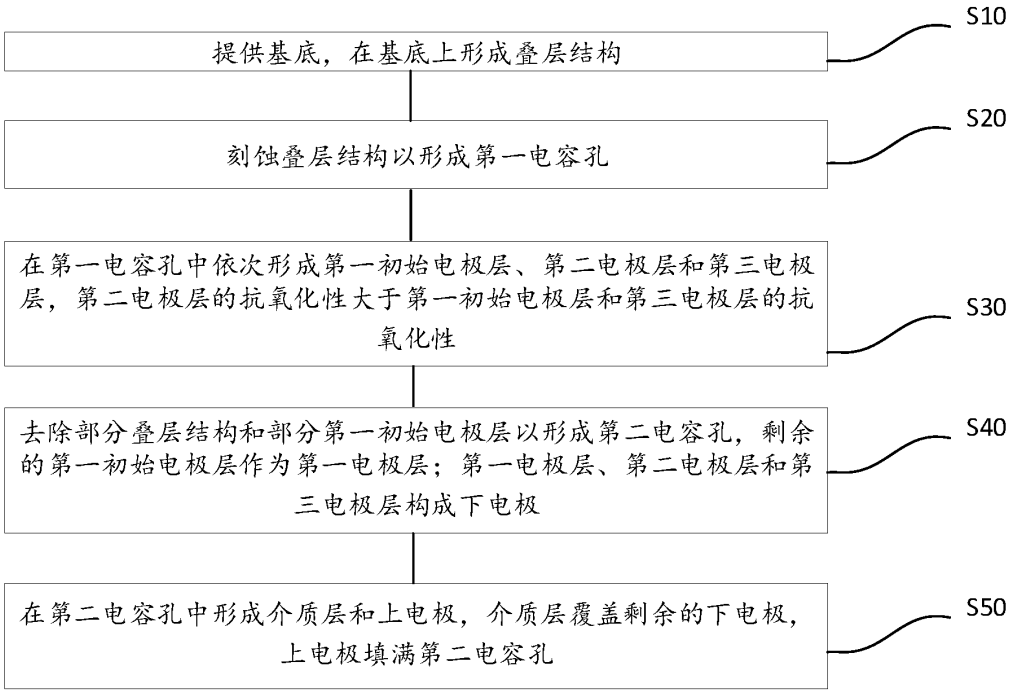

提供基底，在基底上形成叠层结构
S10
刻蚀叠层结构以形成第一电容孔
S20
在第一电容孔中依次形成第一初始电极层、第二电极层和第三电极层，第二电极层的抗氧化性大于第一初始电极层和第三电极层的抗氧化性
S30
去除部分叠层结构和部分第一初始电极层以形成第二电容孔，剩余的第一初始电极层作为第一电极层；第一电极层、第二电极层和第三电极层构成下电极
S40
在第二电容孔中形成介质层和上电极，介质层覆盖剩余的下电极，上电极填满第二电容孔
S50

图 1

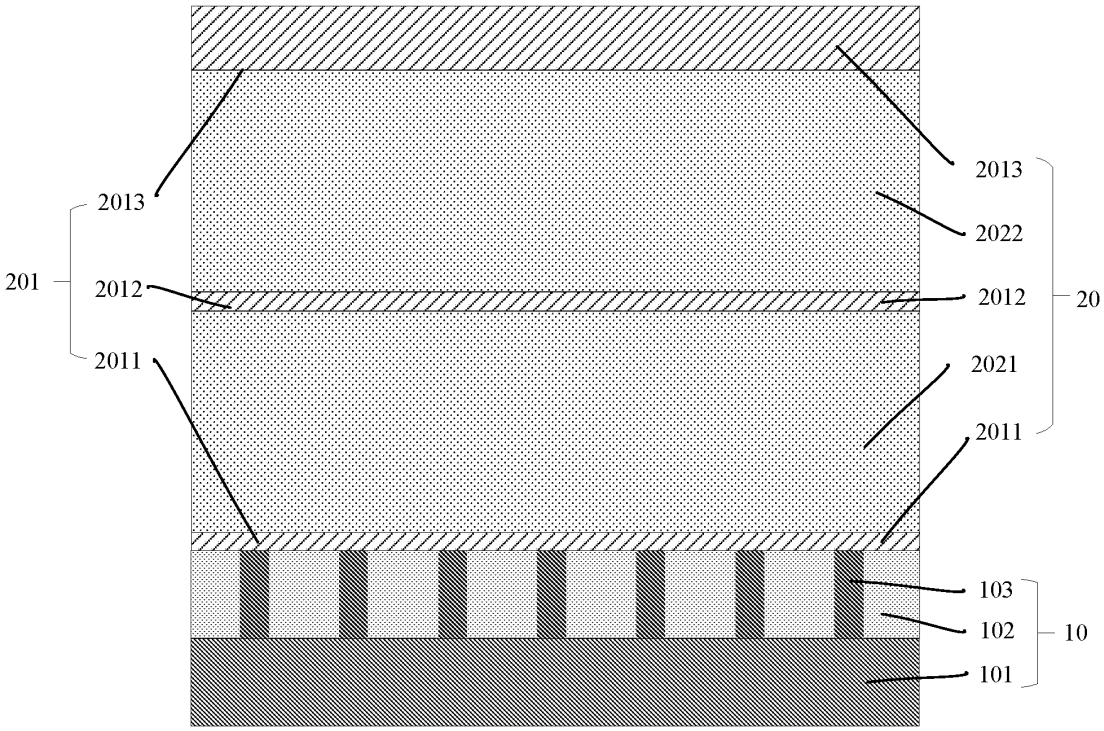

2013
2013
201
2022
2012
2012
20
2011
2021
2011
103
102
10
101

图 2A

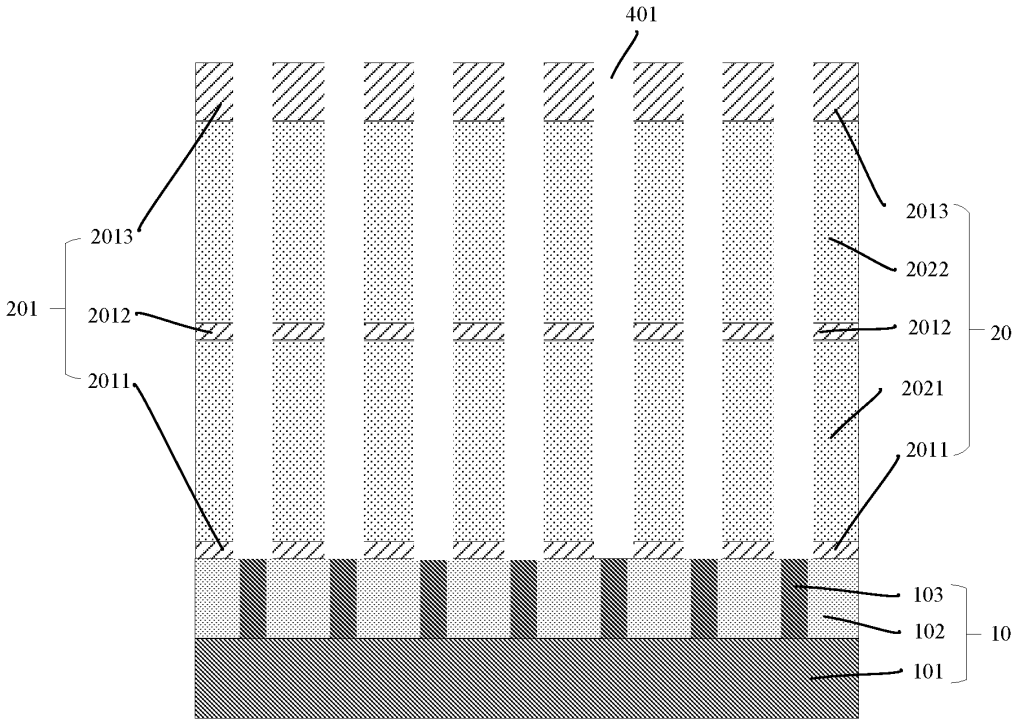

401
2013
201
2012
2011
2013
2022
2012
20
2021
2011
103
102
10
101

图 2B

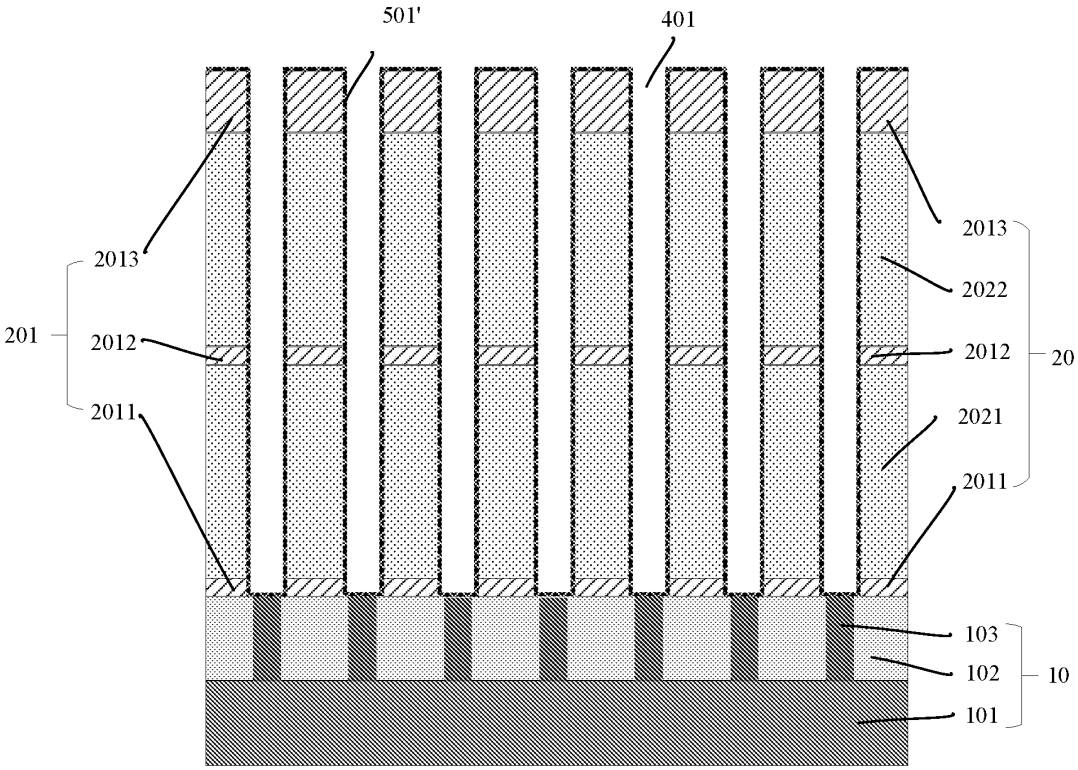

501'
401
2013
201
2012
2011
2013
2022
2012
20
2021
2011
103
102
10
101

图 2C

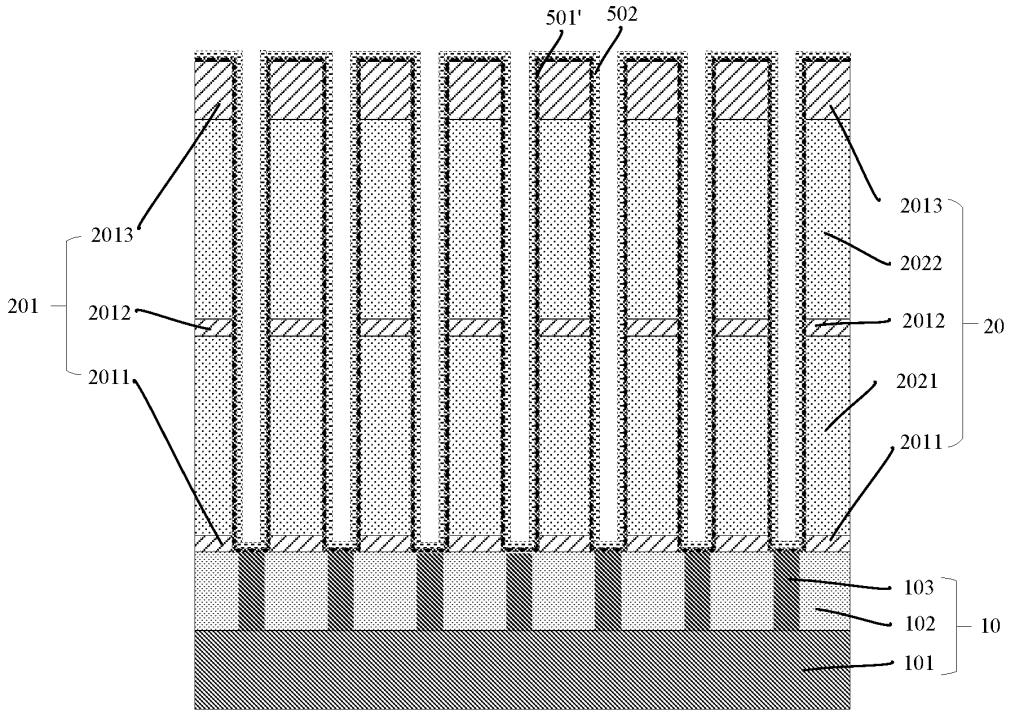

501'
502
2013
2013
201
2022
2012
2012
20
2011
2021
2011
103
102
10
101

图 2D

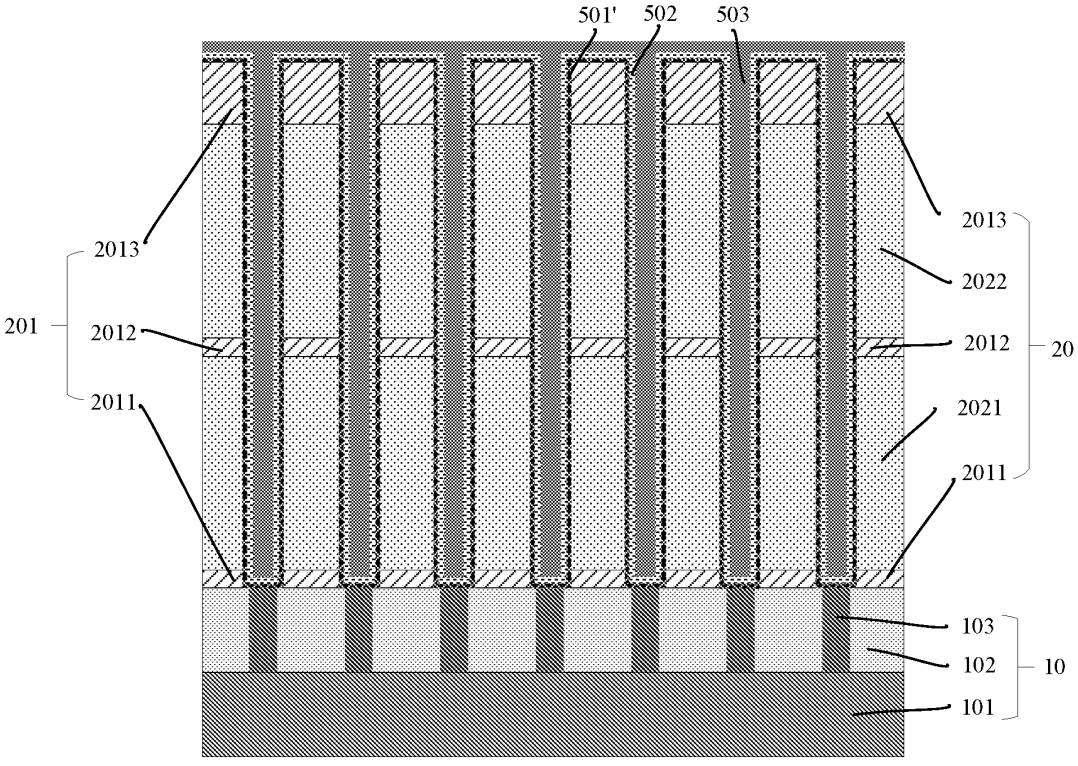

501'
502
503
2013
2013
2022
201
2012
2012
20
2011
2021
2011
103
102
10
101

图 2E

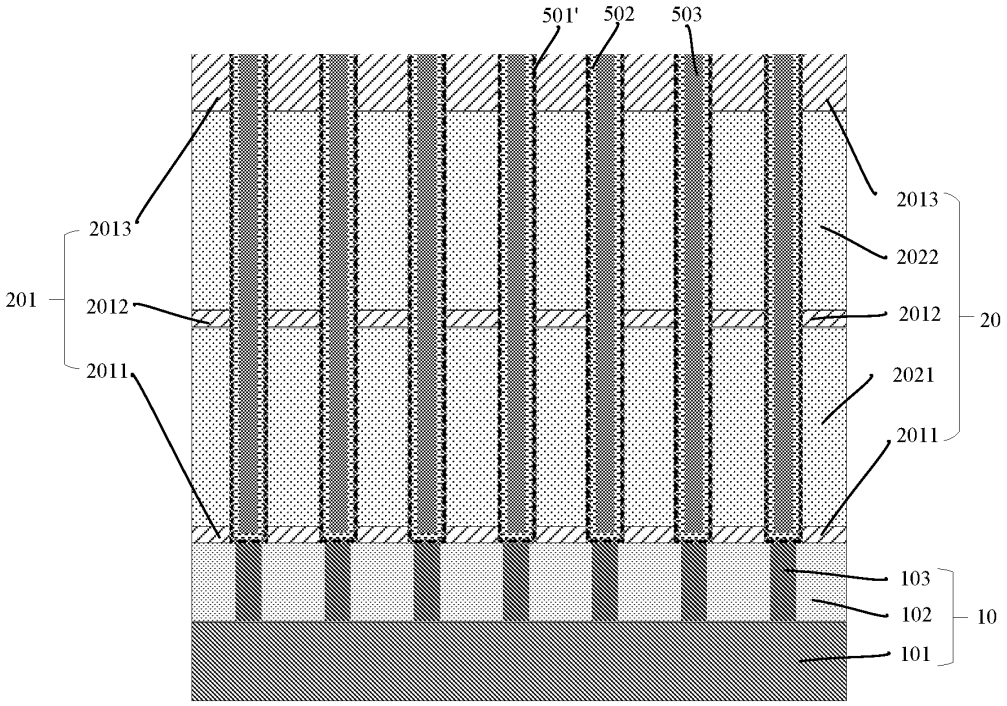

501'
502
503
2013
2013
201
2022
2012
2012
20
2011
2021
2011
103
102
10
101

图 2F

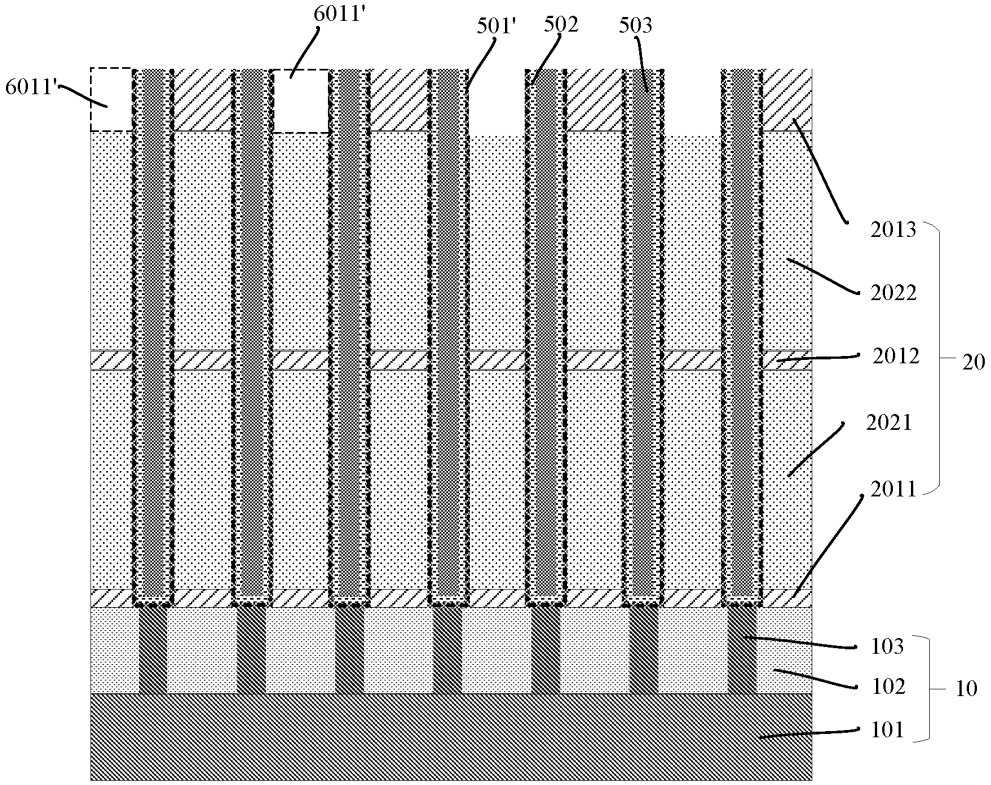

6011'
501'
502
503
6011'
2013
2022
2012
20
2021
2011
103
102
10
101

图 2G

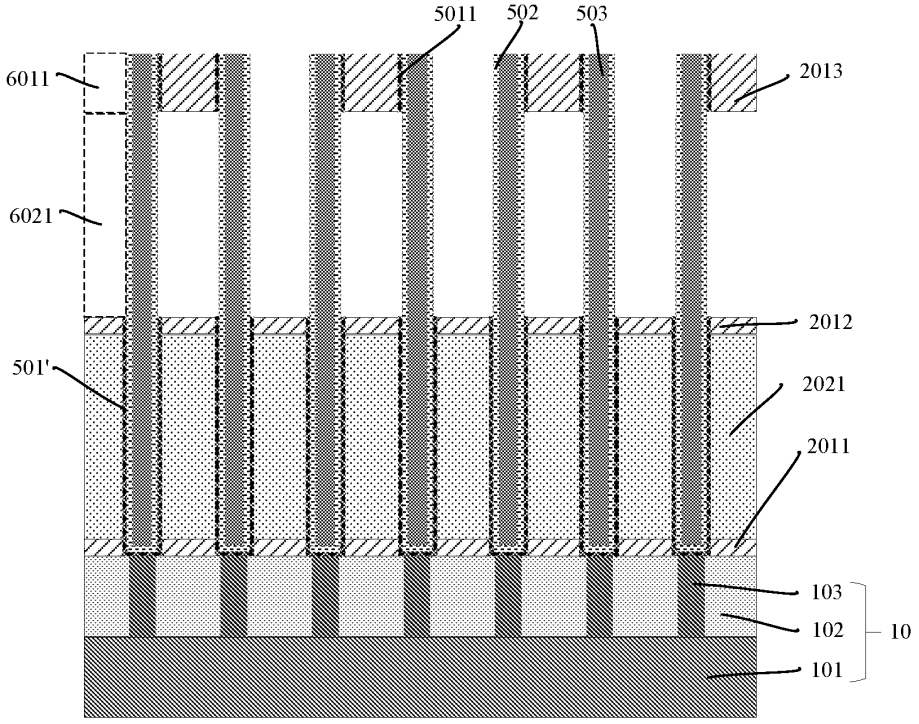

5011
502
503
6011
2013
6021
2012
501'
2021
2011
103
102
10
101

图 2H

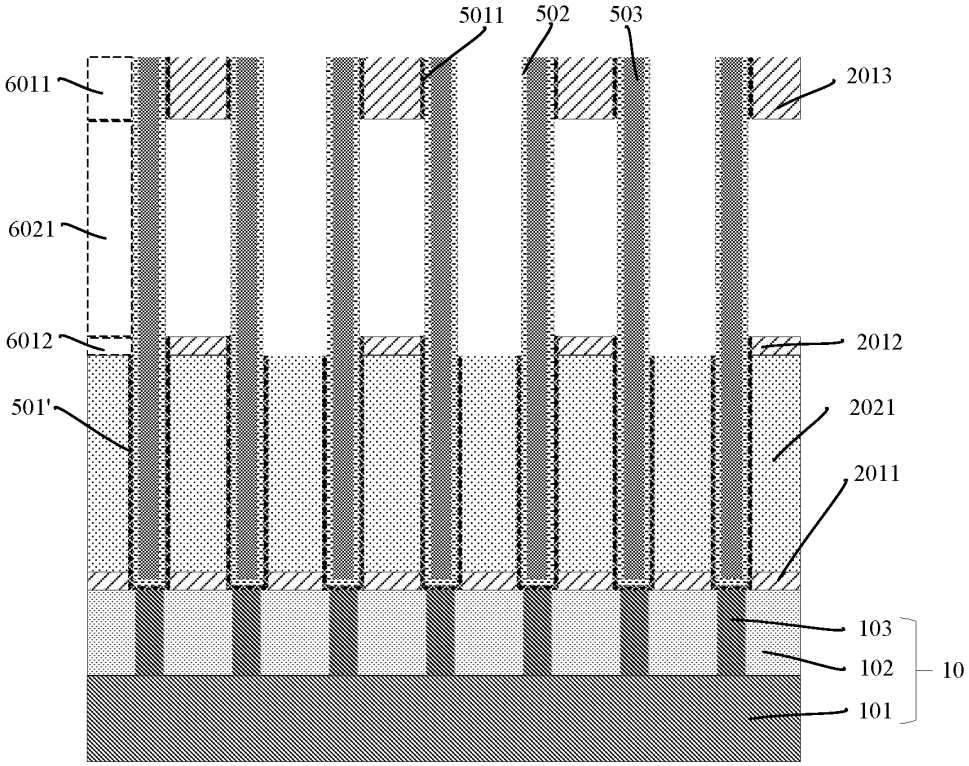

5011
502
503
6011
2013
6021
6012
2012
501'
2021
2011
103
102
10
101

图 2I

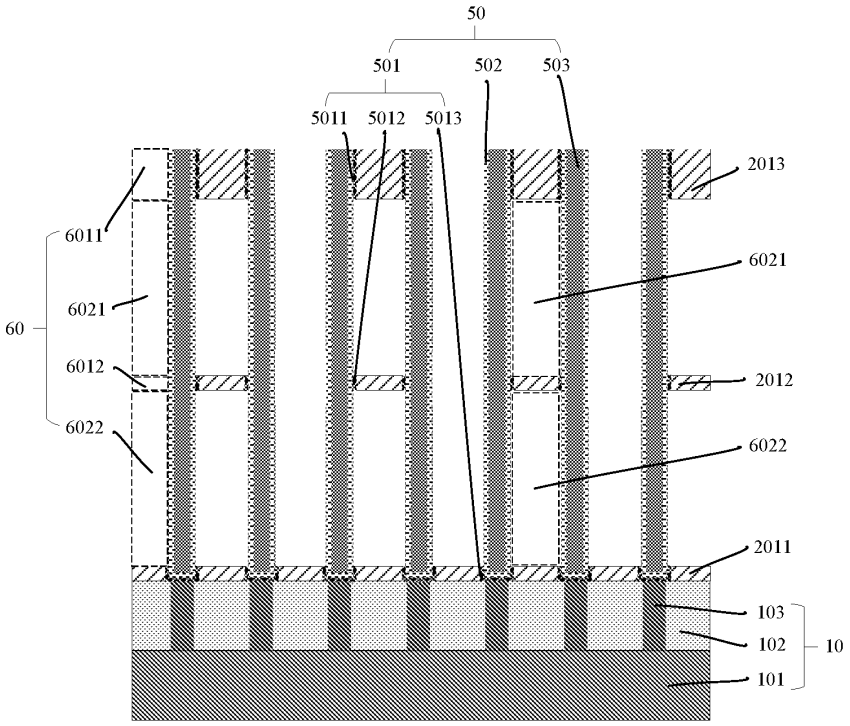

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501
502
503
5011
5012
5013
2013
6011
6021
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6021
6012
2012
6022
6022
2011
103
102
10
101

图 2J

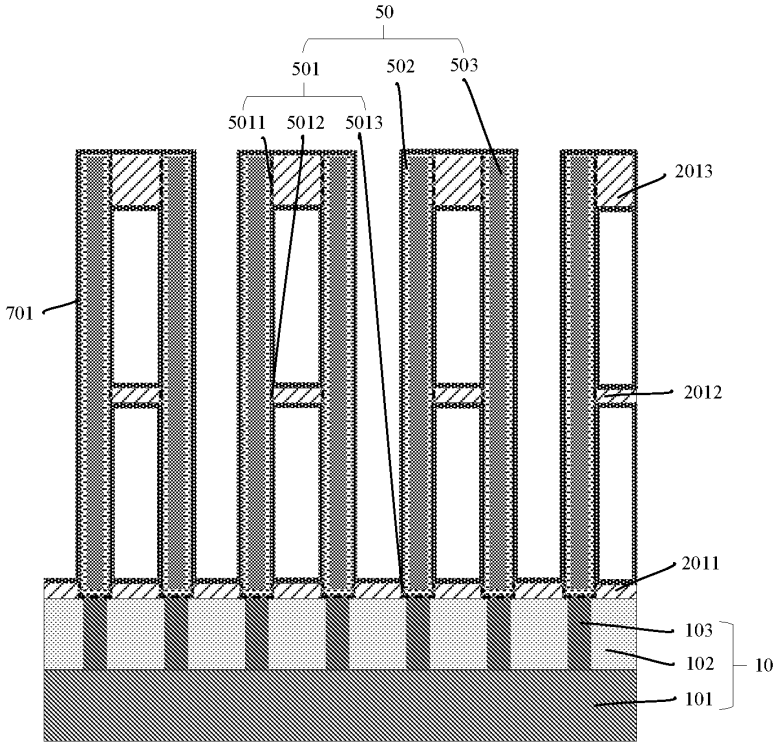

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501
502
503
5011
5012
5013
2013
701
2012
2011
103
102
10
101

图 2K

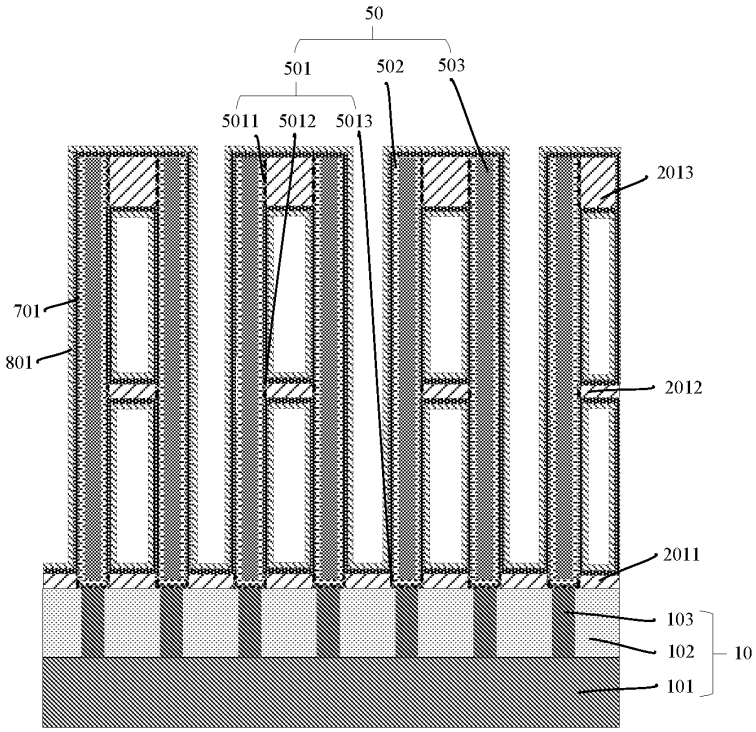

50
501
502
503
5011
5012
5013
2013
701
801
2012
2011
103
102
10
101

图 2L

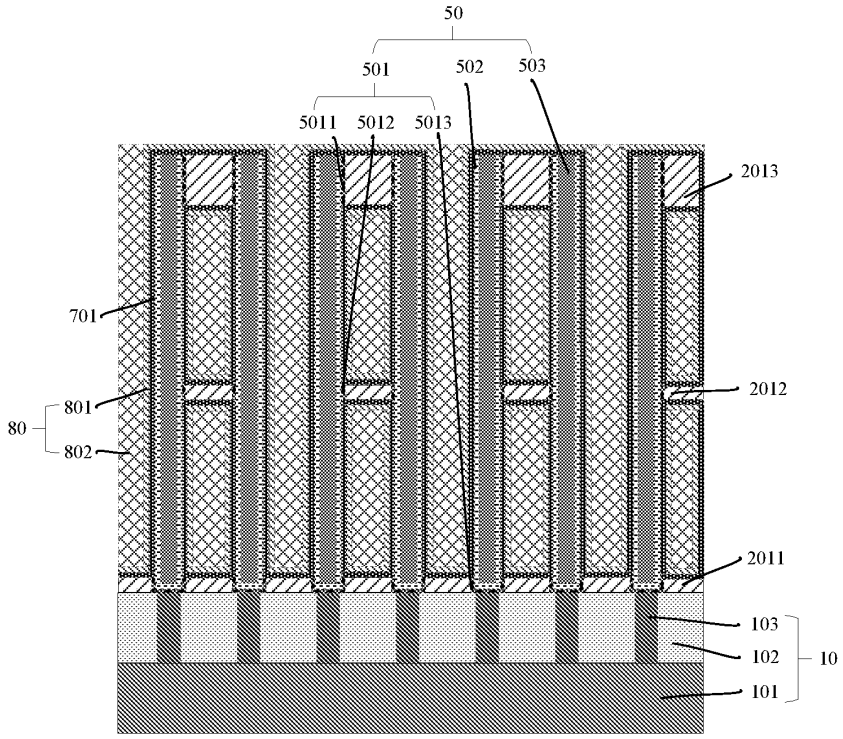

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501
502
503
5011
5012
5013
2013
701
2012
801
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802
2011
103
102
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101

图 2M

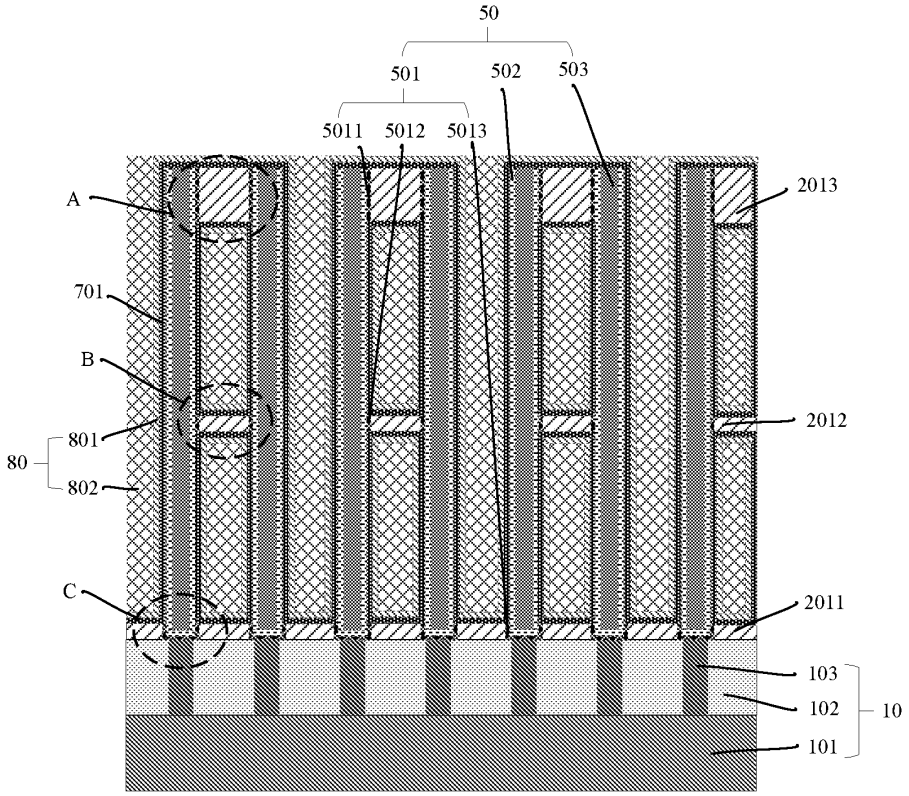

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501
502
503
5011
5012
5013
A
2013
701
B
2012
801
80
802
C
2011
103
102
10
101

图 3

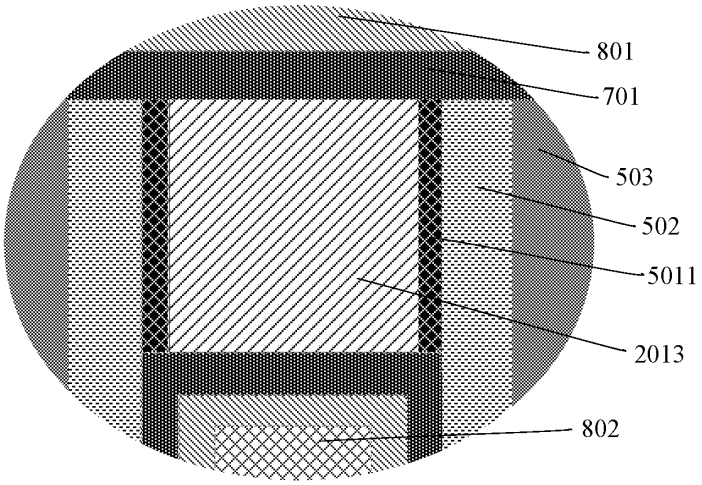

801
701
503
502
5011
2013
802

图 4

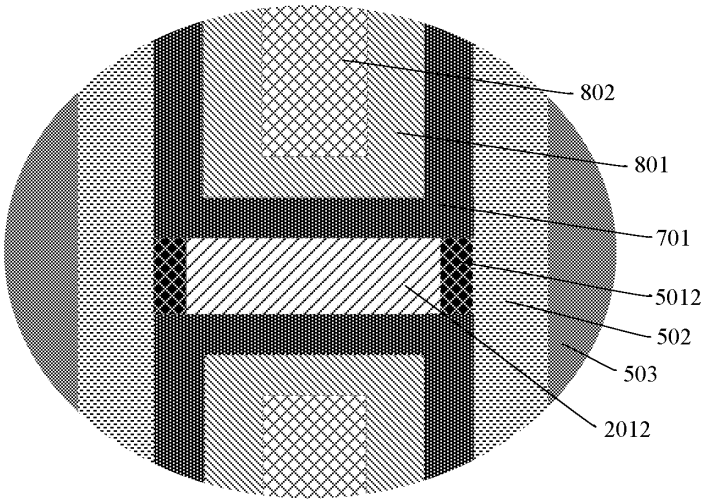

802
801
701
5012
502
503
2012

图 5

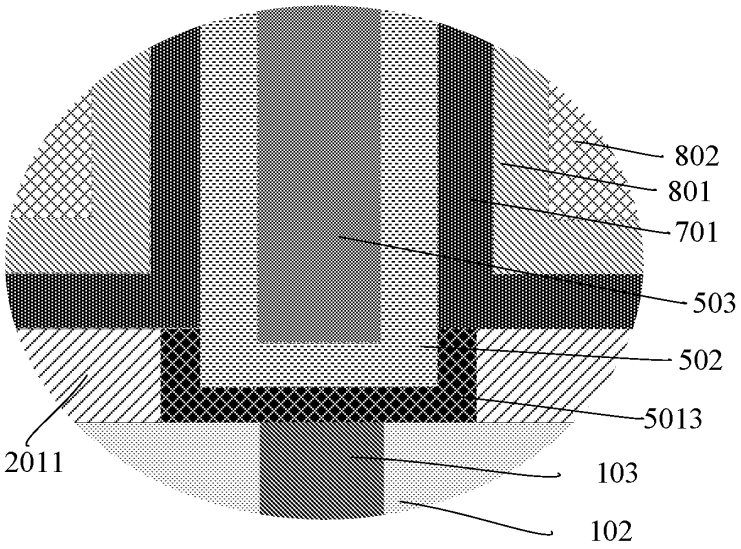

802
801
701
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502
5013
2011
103
102

图 6